

Abstract of the Disclosure

A semiconductor device comprises a device isolation layer disposed in a portion of a substrate of first conductivity type. An outline of the device isolation layer defines an active region of the substrate. An impurity diffused region of second conductivity type may be formed in a portion of the active region; and a silicide layer may be formed to cover the impurity diffused region of second conductivity type. The device isolation layer may include a recess formed therein to expose a portion of the substrate of first conductivity type adjacent to the impurity diffused region of second conductivity type. The silicide layer that is formed to cover the impurity diffused layer of second conductivity type may extend over and against the exposed region of the substrate of first conductivity type that was exposed by the recess of the device isolation layer.